

Silicon Diode

1N4005GP

600V / 1A

DATASHEET

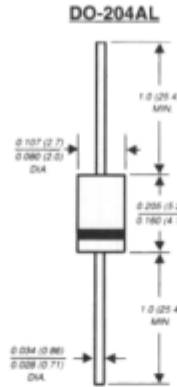
OEM – General Semiconductor

Source: General Semiconductor Databook 1998

1N4001GP THRU 1N4007GP

GLASS PASSIVATED JUNCTION RECTIFIER
Reverse Voltage - 50 to 1000 Volts Forward Current - 1.0 Ampere

PATENTED*



NOTE: Lead diameter is 0.026 (0.66) for suffix "1" part numbers

Dimensions in inches and (millimeters)

* Glass-plastic encapsulation technique is covered by Patent No. 3,996,602 and brazed-lead assembly by Patent No. 3,930,306



FEATURES

- ◆ Plastic package has Underwriters Laboratory Flammability Classification 94V-0
- ◆ High temperature metallurgically bonded construction
- ◆ Glass passivated cavity-free junction
- ◆ Capable of meeting environmental standards of MIL-S-19500
- ◆ 1.0 Ampere operation at $T_A=75^\circ\text{C}$ with no thermal runaway
- ◆ Typical I_R less than $0.1\mu\text{A}$
- ◆ High temperature soldering guaranteed: $350^\circ\text{C}/10$ seconds, 0.375" (9.5mm) lead length, 5 lbs. (2.3kg) tension

MECHANICAL DATA

Case: JEDEC DO-204AL molded plastic over glass body
Terminals: Plated axial leads, solderable per MIL-STD-750, Method 2026
Polarity: Color band denotes cathode end
Mounting Position: Any
Weight: 0.012 ounce, 0.3 gram

MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Ratings at 25°C ambient temperature unless otherwise specified.

	SYMBOLS	1N 4001GP	1N 4002GP	1N 4003GP	1N 4004GP	1N 4005GP	1N 4006GP	1N 4007GP	UNITS
* Maximum repetitive peak reverse voltage	VRRM	50	100	200	400	600	800	1000	Volts
* Maximum RMS voltage	VRMS	35	70	140	280	420	560	700	Volts
* Maximum DC blocking voltage	VDC	50	100	200	400	600	800	1000	Volts
* Maximum average forward rectified current 0.375" (9.5mm) lead length at $T_A=75^\circ\text{C}$	$I_{(AV)}$	1.0							Amp
* Peak forward surge current 8.3ms single half sine-wave superimposed on rated load (JEDEC Method)	IFSM	30.0							Amps
Maximum instantaneous forward voltage at 1.0A	V _F	1.1							Volts
* Maximum full load reverse current, full cycle average 0.375" (9.5mm) lead length $T_A=75^\circ\text{C}$	$I_{R(AV)}$	30.0							μA
* Maximum DC reverse current at rated DC blocking voltage $T_A=25^\circ\text{C}$ $T_A=125^\circ\text{C}$	I_R	5.0 50.0							μA
Typical reverse recovery time (NOTE 1)	t_{rr}	2.0							μs
Typical junction capacitance (NOTE 2)	C _J	8.0							pF
Typical thermal resistance (NOTE 3)	R _{θJA} R _{θJL}	55.0 25.0							$^\circ\text{C}/\text{W}$
* Operating junction and storage temperature range	T _J , T _{STG}	-65 to +175							$^\circ\text{C}$

NOTES:

- (1) Reverse recovery test conditions: $I_F=0.5\text{A}$, $I_{FSM}=1.0\text{A}$, $I_{RR}=0.25\text{A}$
 - (2) Measured at 1.0 MHz and applied reverse voltage of 4.0 Volts
 - (3) Thermal resistance from junction to ambient at 0.375" (9.5mm) lead length, P.C.B. mounted
- *JEDEC registered values

RATINGS AND CHARACTERISTIC CURVES 1N4001GP THRU 1N4007GP

